

Features

- Trench LV MOSFET Technology
- Low RDS(on)
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Dual N&P-Channel MOSFET

Maximum Ratings

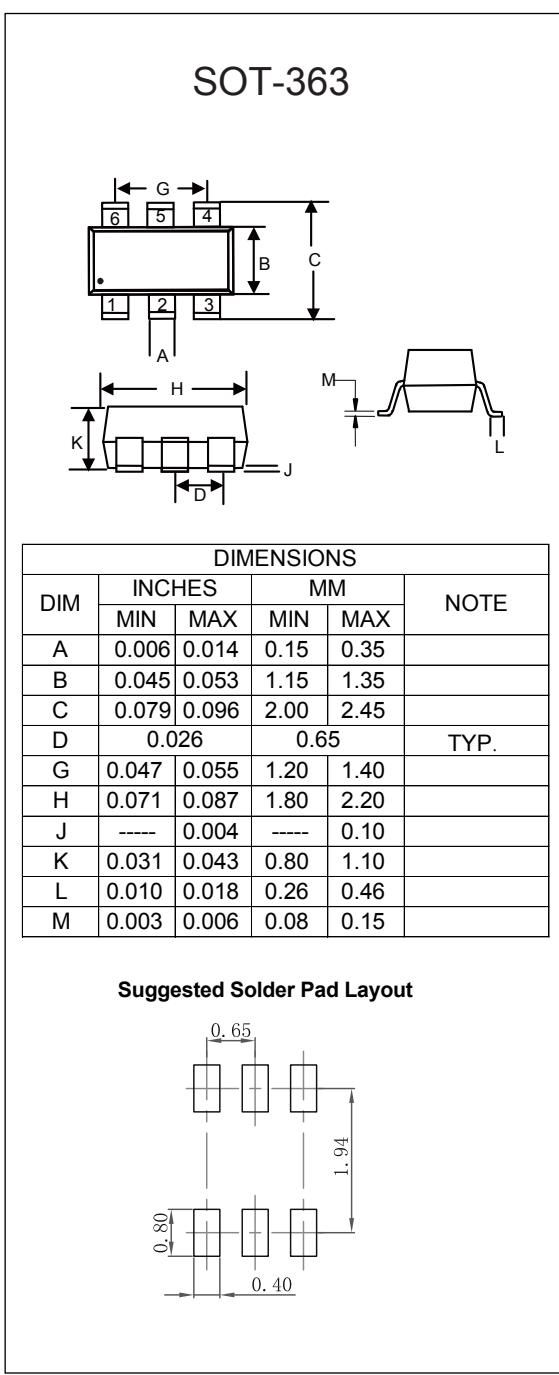
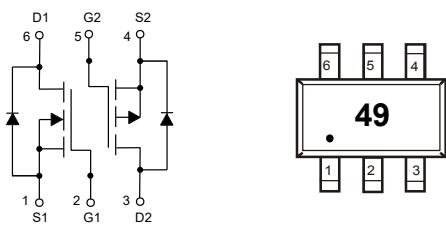
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 290°C/W Junction to Ambient^(Note 2)

Parameter	Symbol	Rating	Unit
Total Power Dissipation ^(Note 4)	P _D	0.43	mW
N-Channel MOSFET			
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±10	V
Continuous Drain Current	I _D	1.5	A
		0.95	
Pulsed Drain Current ^(Note 3)	I _{DM}	6	A
P-Channel MOSFET			
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±10	V
Continuous Drain Current	I _D	-1	A
		-0.63	
Pulsed Drain Current ^(Note 3)	I _{DM}	-4	A

Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

Internal Structure and Marking Code



N-Channel MOSFET Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.55	0.75	1.1	V
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=1A$		75	90	$m\Omega$
		$V_{GS}=2.5V, I_D=0.6A$		86	105	
		$V_{GS}=1.8V, I_D=0.3A$		110	135	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=1.5A$		7.5		S
Gate Resistance	R_g	f=1 MHz, Open drain		1.8		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				1.5	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1.5A$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F=1.5A, dI_F/dt=100A/\mu s$		9		ns
Reverse Recovery Charge	Q_{rr}			2		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, f=1MHz$		188		pF
Output Capacitance	C_{oss}			35		
Reverse Transfer Capacitance	C_{rss}			29		
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V, I_D=1.5A$		2.7		nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=10V, V_{GS}=4.5V, R_G=3\Omega, I_D=1.5A$		4		ns
Turn-On Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			10		
Turn-Off Fall Time	t_f			2		

P-Channel MOSFET Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.62	-1	V
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-1A$		119	150	mΩ
		$V_{GS}=-2.5V, I_D=-0.6A$		150	180	
		$V_{GS}=-1.8V, I_D=-0.3A$		193	260	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-1A$		4.5		S
Gate Resistance	R_g	f=1 MHz, Open drain		15		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				-1	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-0.5A$			-1.2	V
Reverse Recovery Time	t_{rr}	$I_F=-1A, dI_F/dt=100A/\mu s$		13		ns
Reverse Recovery Charge	Q_{rr}			3		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, f=1MHz$		220		pF
Output Capacitance	C_{oss}			35		
Reverse Transfer Capacitance	C_{rss}			28		
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-1A$		3.2		nC
Gate-Source Charge	Q_{gs}			0.4		
Gate-Drain Charge	Q_{gd}			0.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=-10V, V_{GS}=-4.5V, R_G=3\Omega, I_D=-1A$		8		ns
Turn-On Rise Time	t_r			6		
Turn-Off Delay Time	$t_{d(off)}$			27		
Turn-Off Fall Time	t_f			12		

Curve Characteristics (N-Channel)

Fig.1 - Typical Output Characteristics

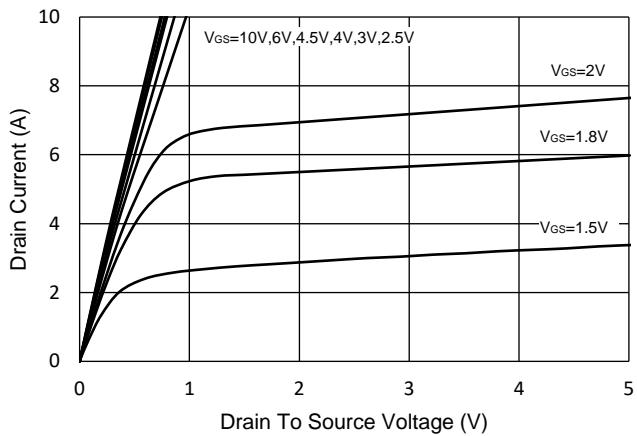


Fig.2 - Transfer Characteristic

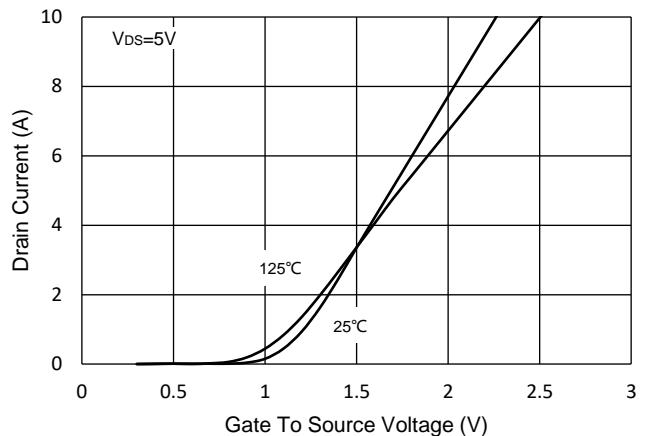


Fig.3 - $R_{DS(ON)}$ - V_{GS}

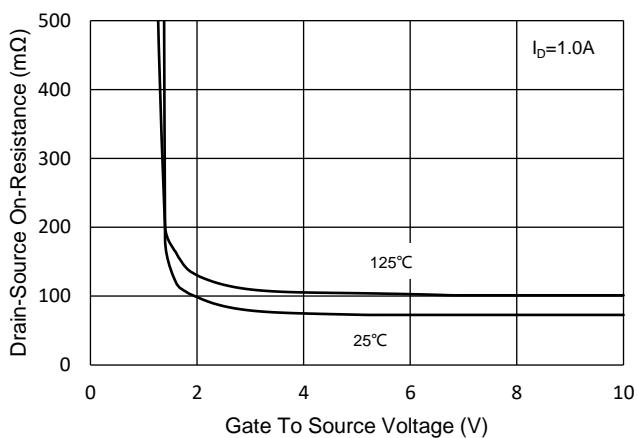


Fig.4 - $R_{DS(ON)}$ - I_D

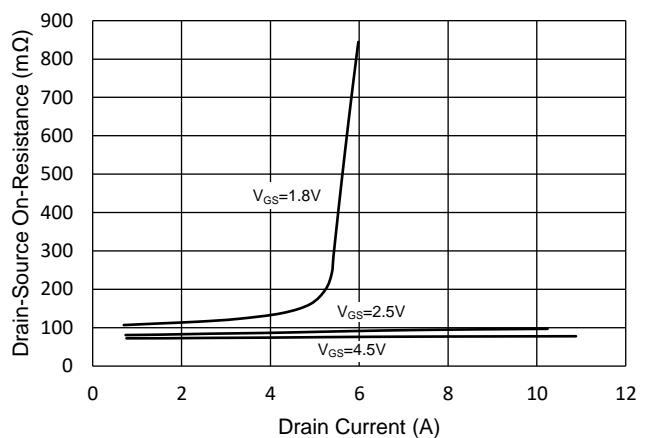


Fig.5 - Capacitance Characteristics

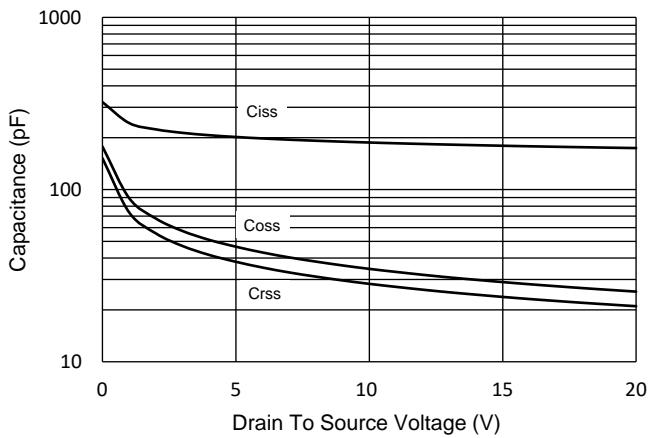
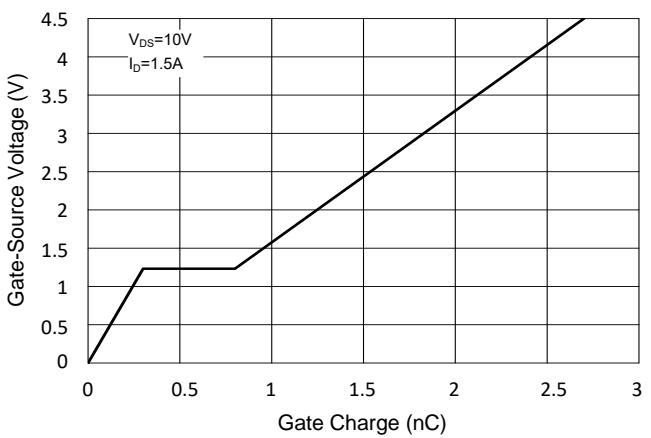


Fig.6 - Gate Charge



Curve Characteristics (N-Channel)

Fig.7 - Normalized Threshold Voltage

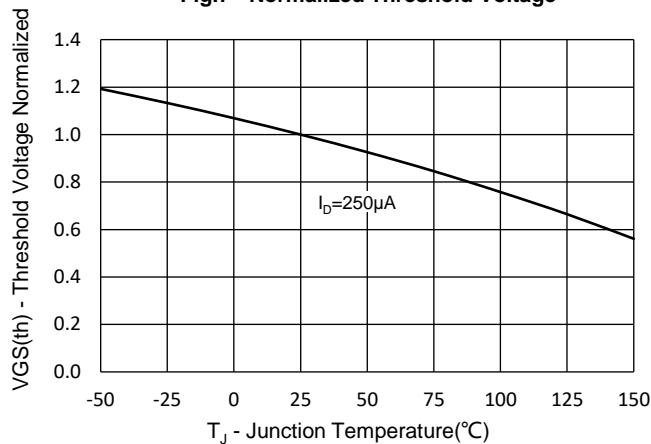


Fig.8 - Normalized On Resistance Characteristics

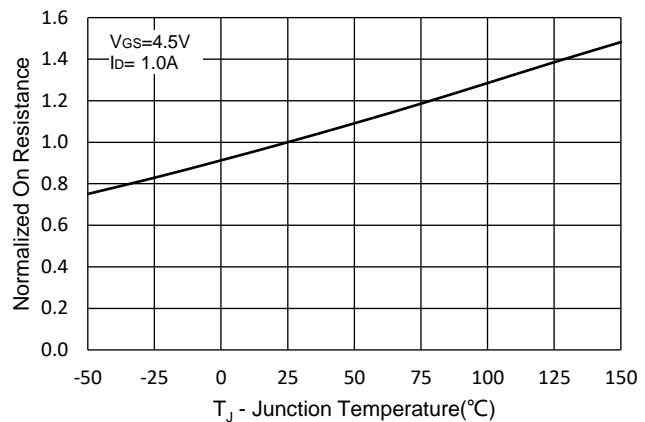


Fig.9 - I_S - V_{SD}

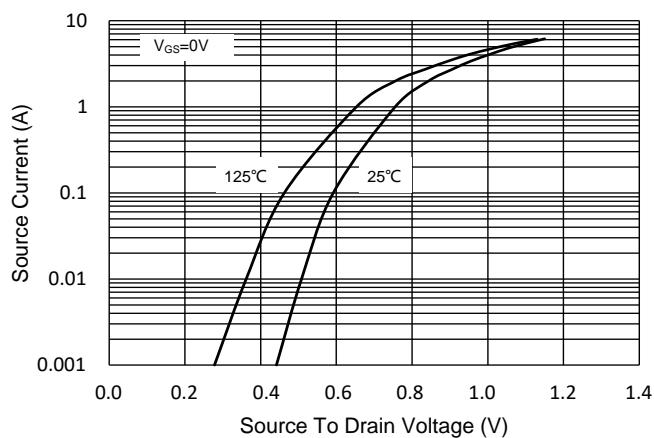


Fig.10 - Drain Current

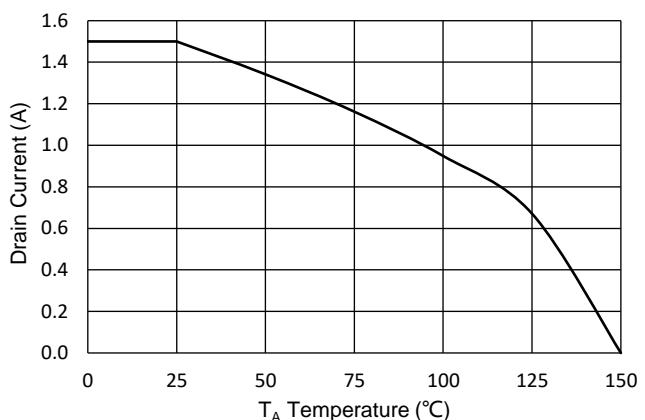
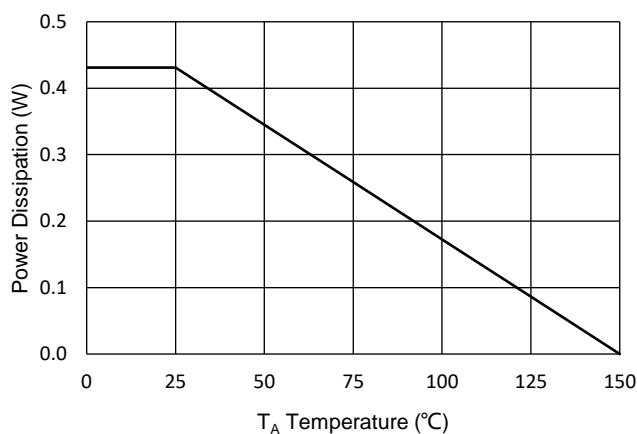


Fig.11 - PD Dissipation



Curve Characteristics (N-Channel)

Fig.12 - Safe Operation Area

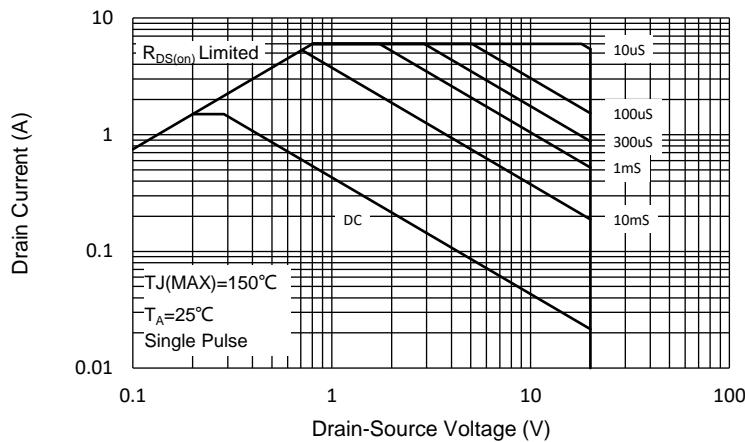
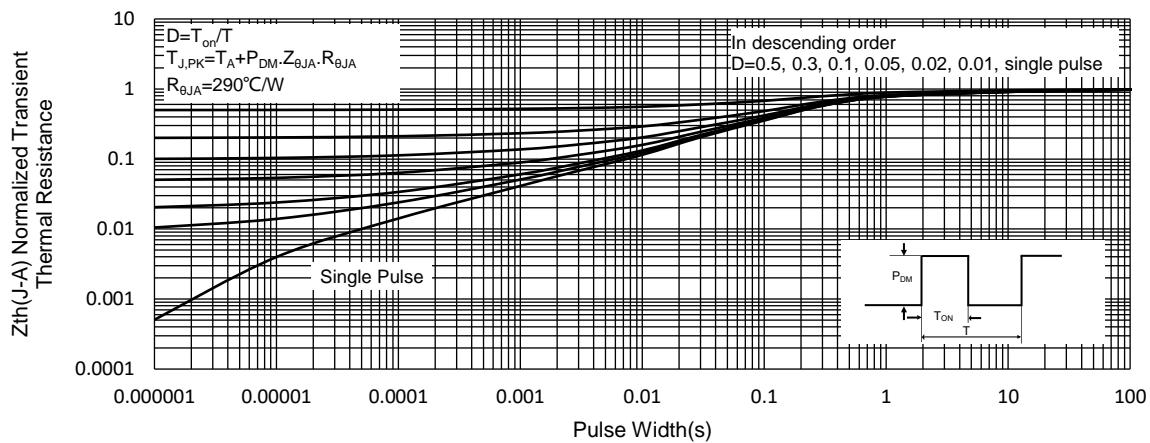


Fig.13 - Normalized Transient Thermal Impedance



Curve Characteristics (P-Channel)

Fig.1 - Typical Output Characteristics

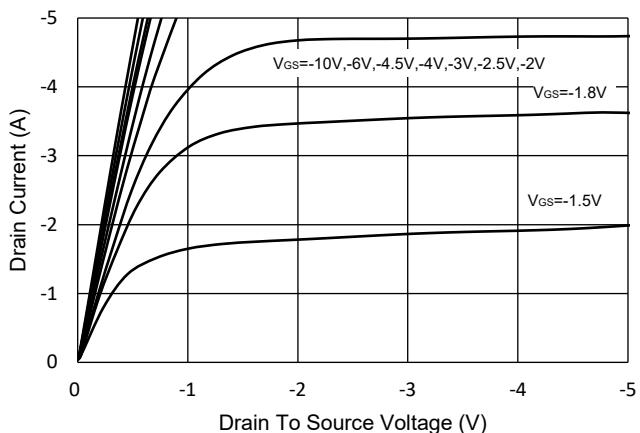


Fig.2 - Transfer Characteristic

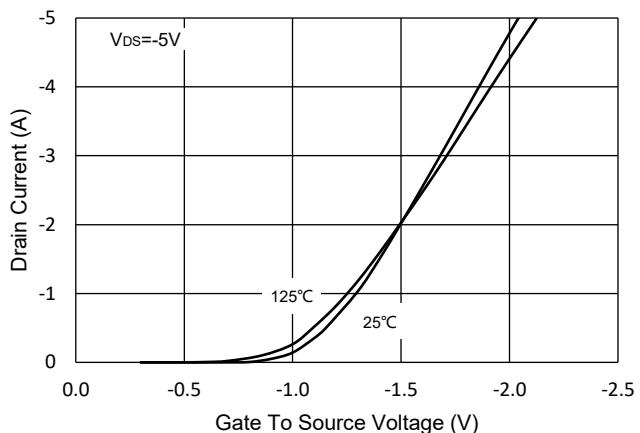


Fig.3 - $R_{DS(ON)}$ - V_{GS}

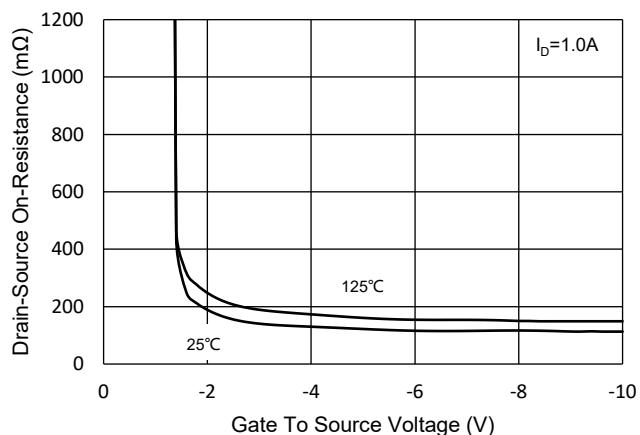


Fig.4 - $R_{DS(ON)}$ - I_D

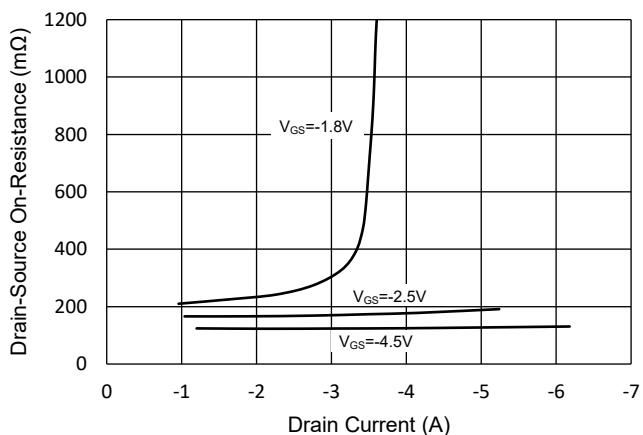


Fig.5 - Capacitance Characteristics

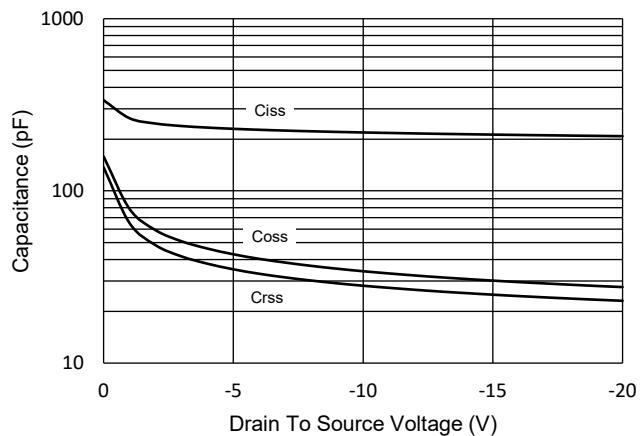
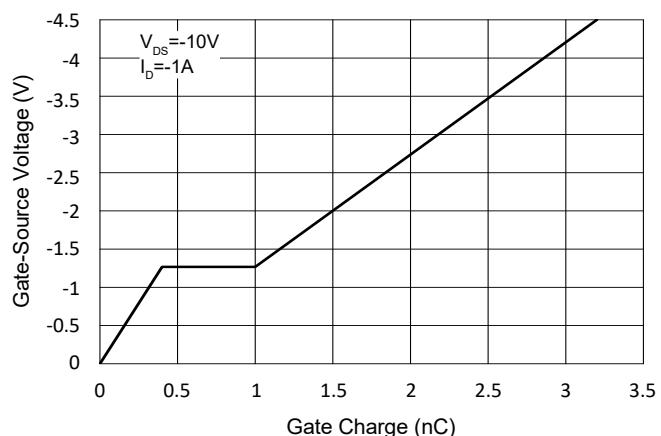


Fig.6 - Gate Charge



Curve Characteristics (P-Channel)

Fig.7 - Normalized Threshold Voltage

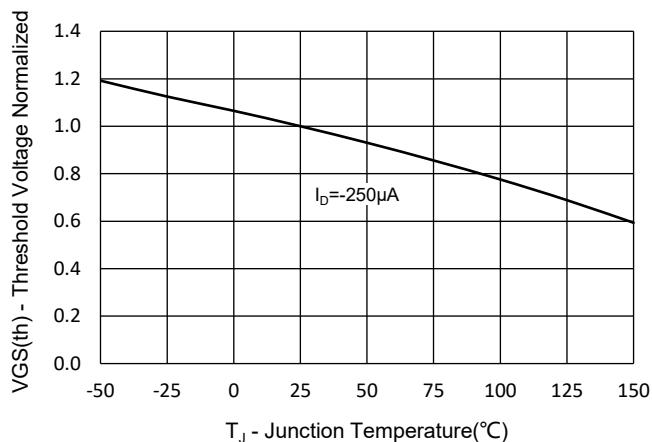


Fig.8 - Normalized On Resistance Characteristics

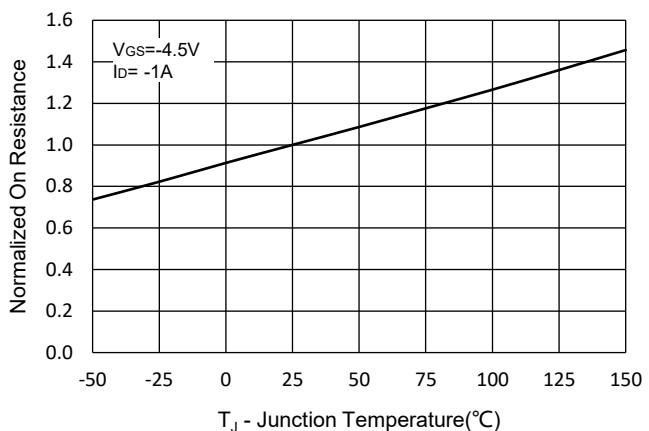


Fig.9 - I_S - V_{SD}

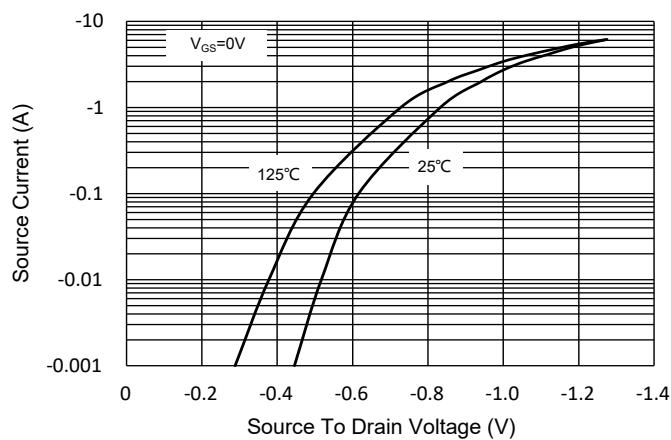


Fig.10 - Drain Current

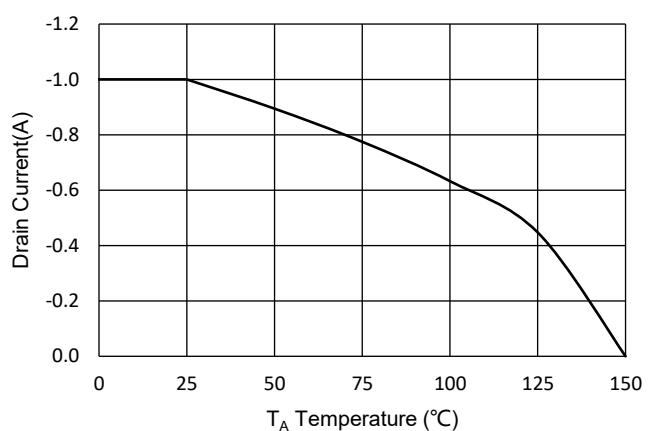
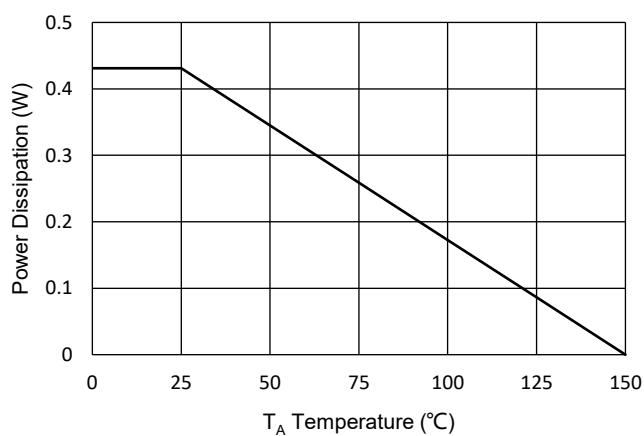


Fig.11 - PD Dissipation



Curve Characteristics (P-Channel)

Fig.12 - Safe Operation Area

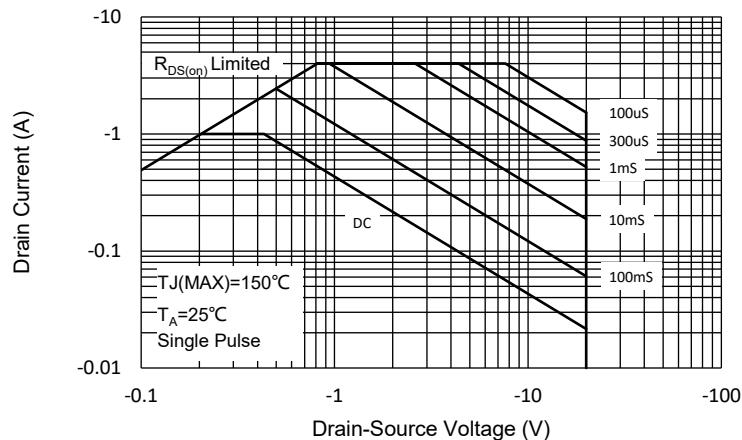
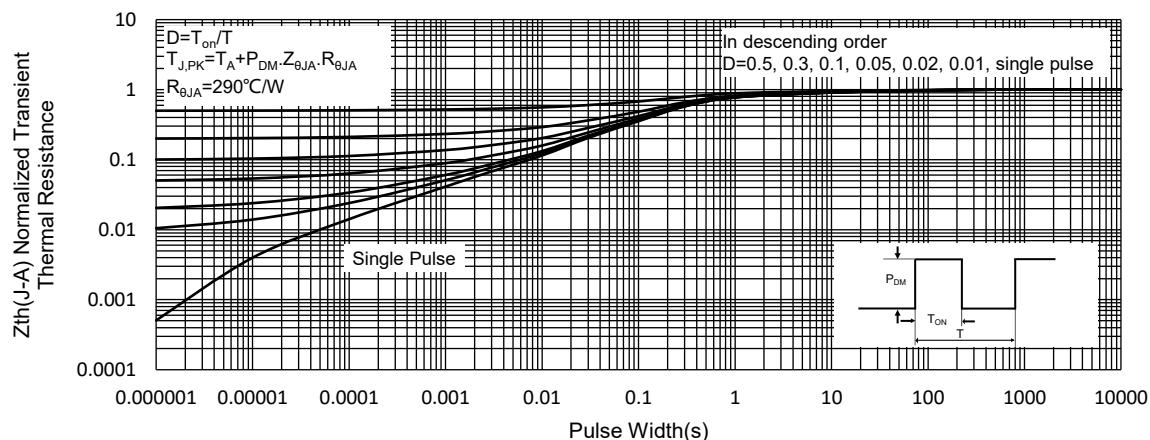


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel

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